Optical Link ASICs for LHC Upgrades

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July 30, 2009

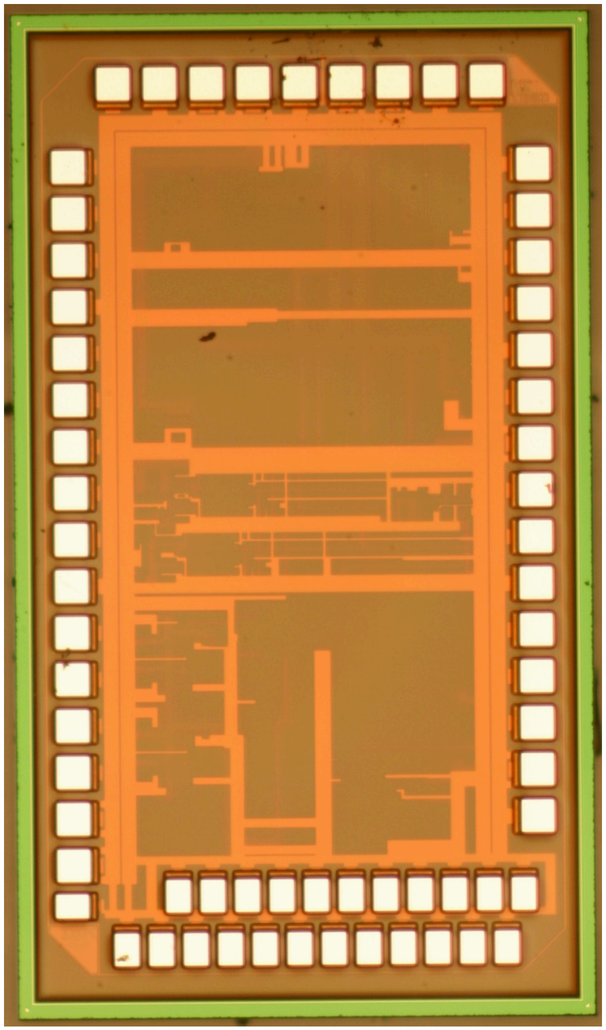
Outline

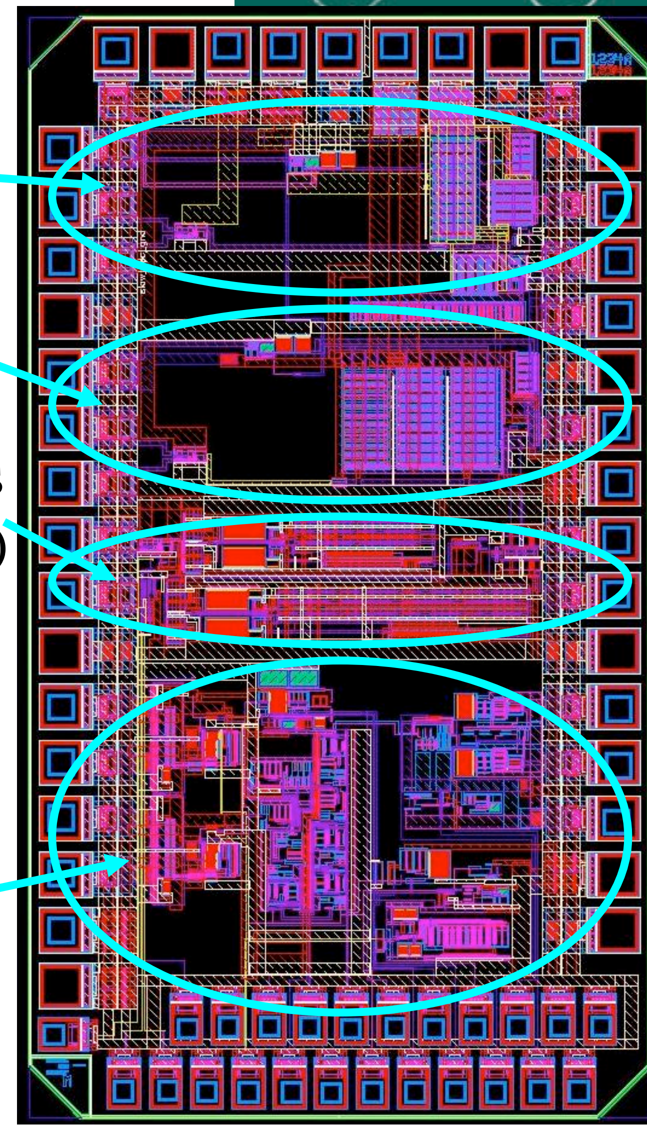
- Introduction
- VCSEL driver chip
- PIN receiver/decoder chip
- Clock multiplier
- Summary

Introduction

- 1st phase of LHC upgrade is planned for 2014:
  - 3 times increase in luminosity to $3x10^{34}$ $cm^{-2}s^{-1}$
  - expect significant degradation in the ATLAS pixel detector
  - ⇨ add an insertable barrel layer (IBL) at radius of 3.5 cm
- Possible upgrade for on-detector optical readout system for the IBL:
  - add new functionalities to correct for deficiencies in current system
  - upgrade current optical chips to run at higher speed
  - some of the development could be of interest to SLHC upgrade
  - use 130 nm CMOS 8RF process
  - prototype chips received/irradiated in July/August 2008
  - ⇨ results will be presented below

Opto-Chips

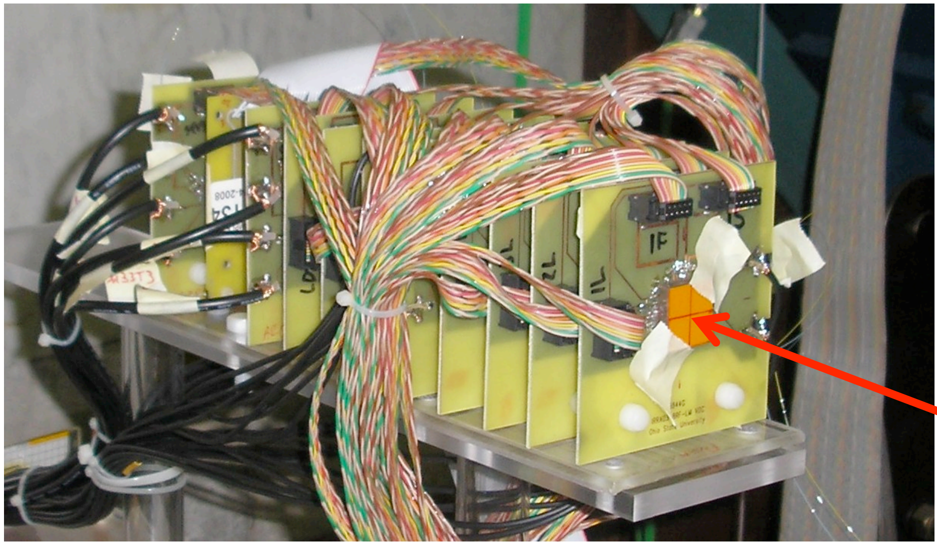




2.6 mm x 1.5 mm

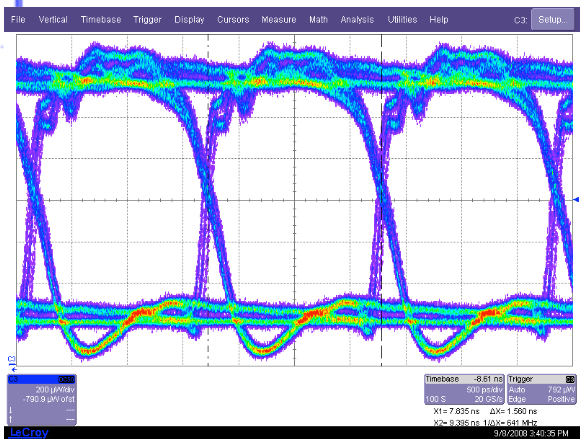
Testing the 130 nm Opto-Chips

- chips were tested in the lab at Ohio State University
- chips were irradiated with 24 GeV protons to SLHC dose at CERN
  - 8 VCSEL drivers: 4 “slow” + 4 “fast”
  - 4 PIN receivers/decoders (purely electrical testing)
  - 4 PIN receivers/decoders coupled to PIN
  - 4 clock multipliers
  - long cables limited testing of drivers/receivers to 40 Mb/s
  - special designed card allows testing of clock multiplier at 640 MHz

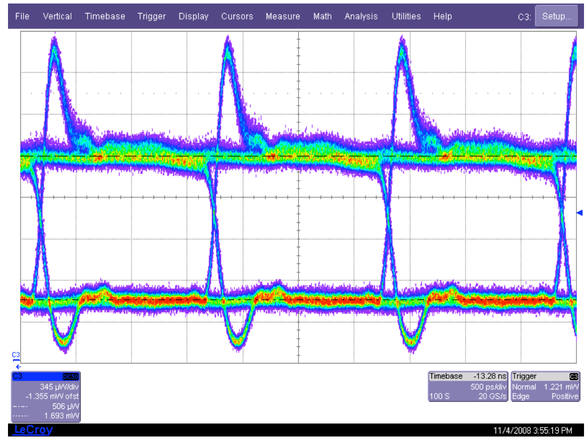


protons

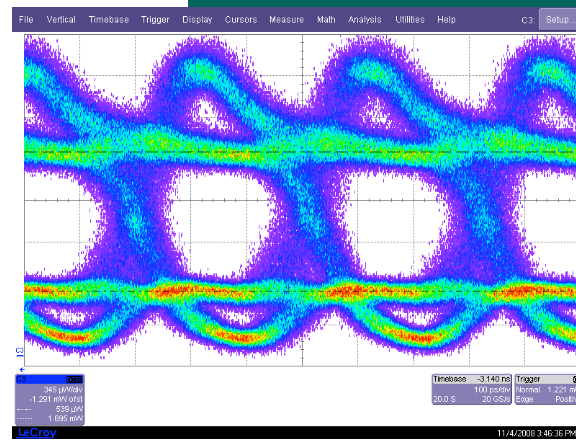
VCSEL Driver Chip



Slow VDC
640 Mb/s
~ 14 mA max



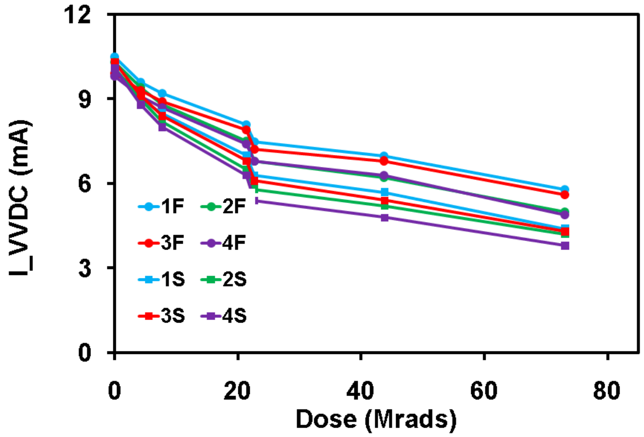
Fast VDC
640 Mb/s
~ 9 mA max

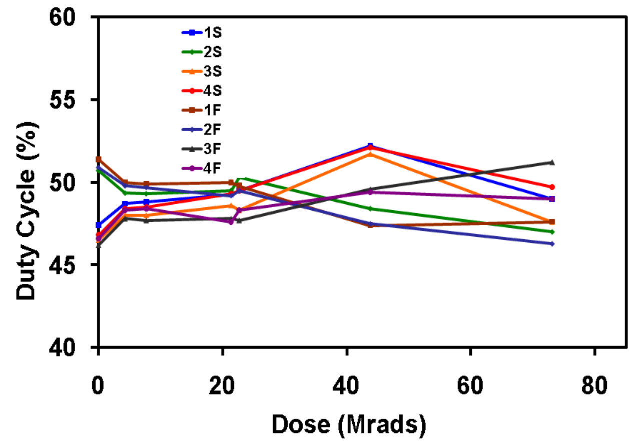


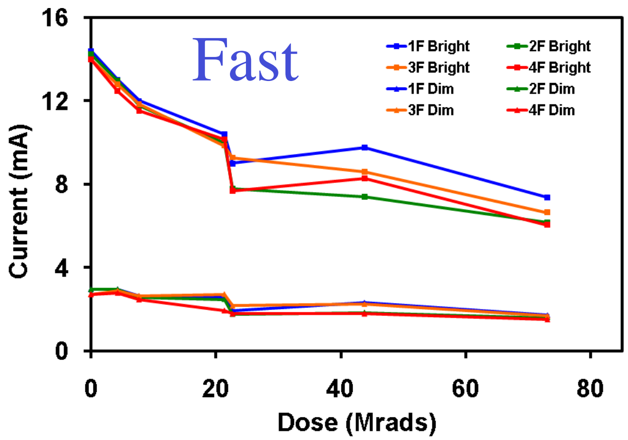
Fast VDC
3.2 Gb/s

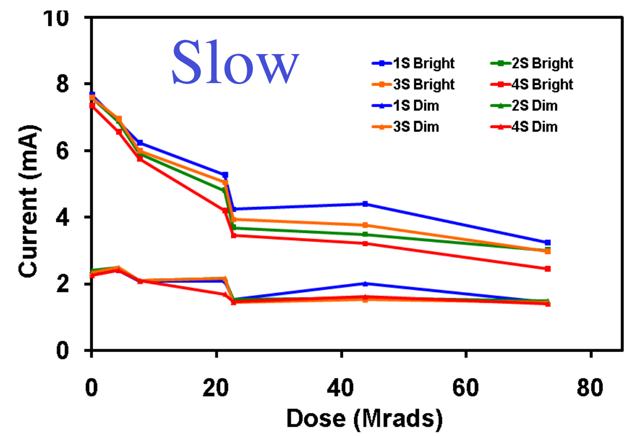
- both slow/fast chips are working
- LVDS receiver/VCSEL driver work at high speed
  - BER < 10^{-13} @ 4 Gb/s using 10 Gb/s AOC VCSEL

VDC Irradiation





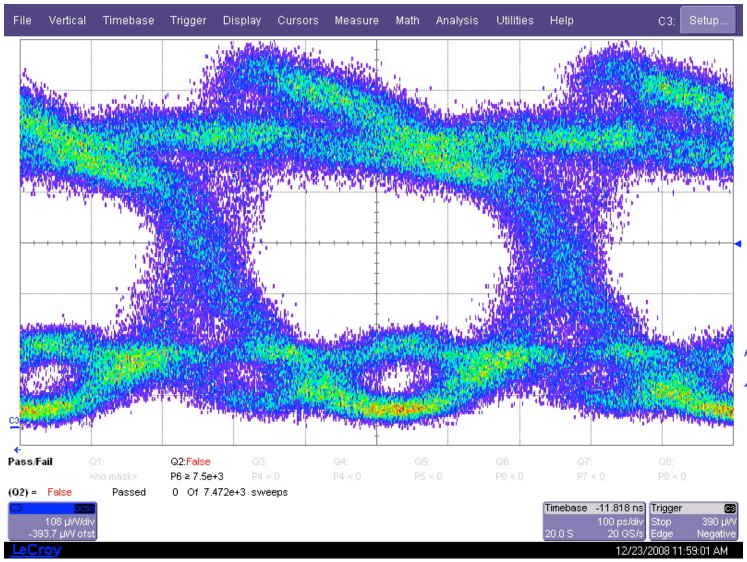




- VDC driving 25 Ω with constant control current (Iset)
- drive current decreases with radiation for constant Iset
  - driver circuit fabricated with thick oxide process

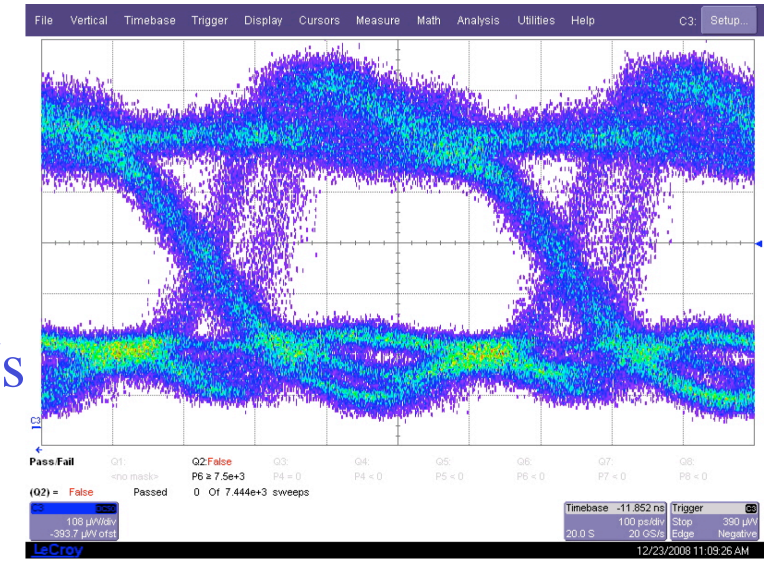
Unirradiated vs. Irradiated VDC

Unirradiated



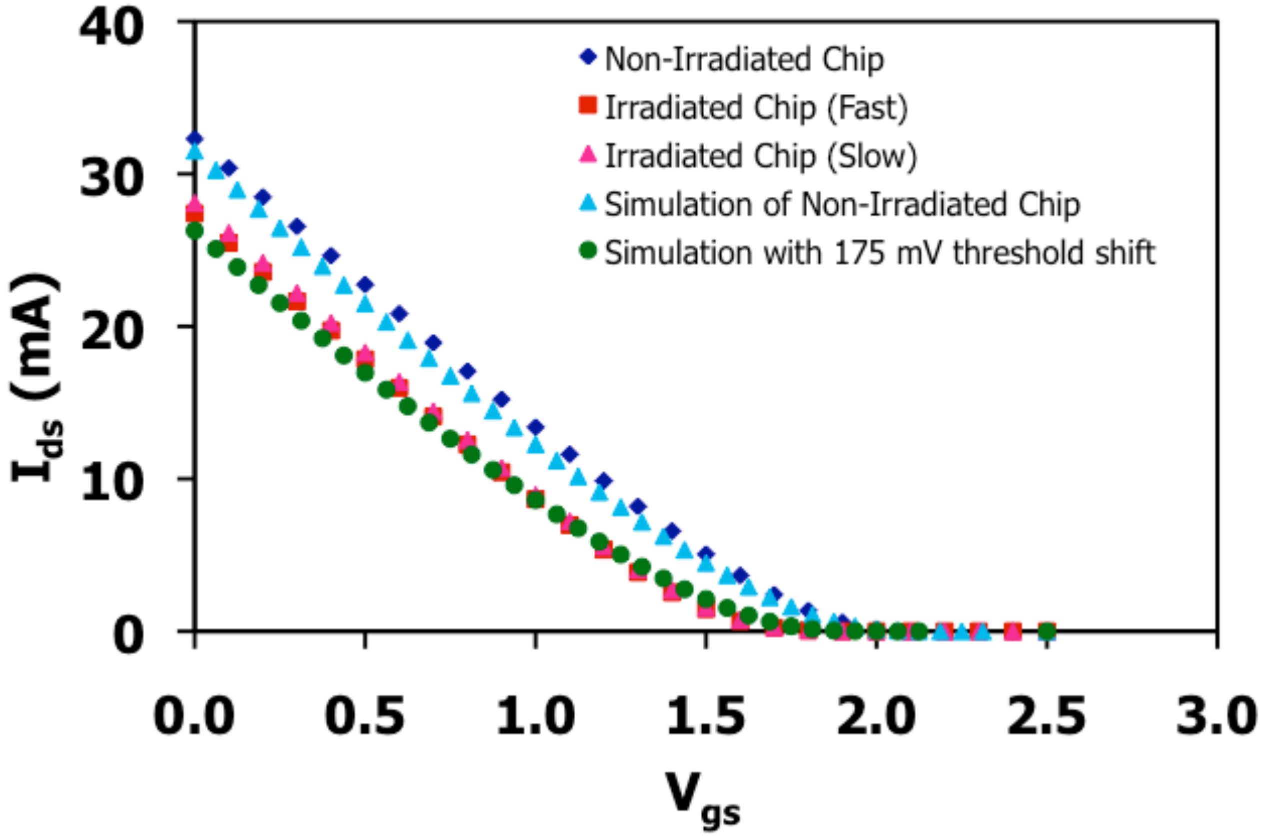
2 Gb/s

Irradiated



- VDC driving 2.5 Gb/s Optowell VCSEL
- Possible to obtain similar eye diagram by adjusting control currents
  - radiation induced changes in control current circuitry

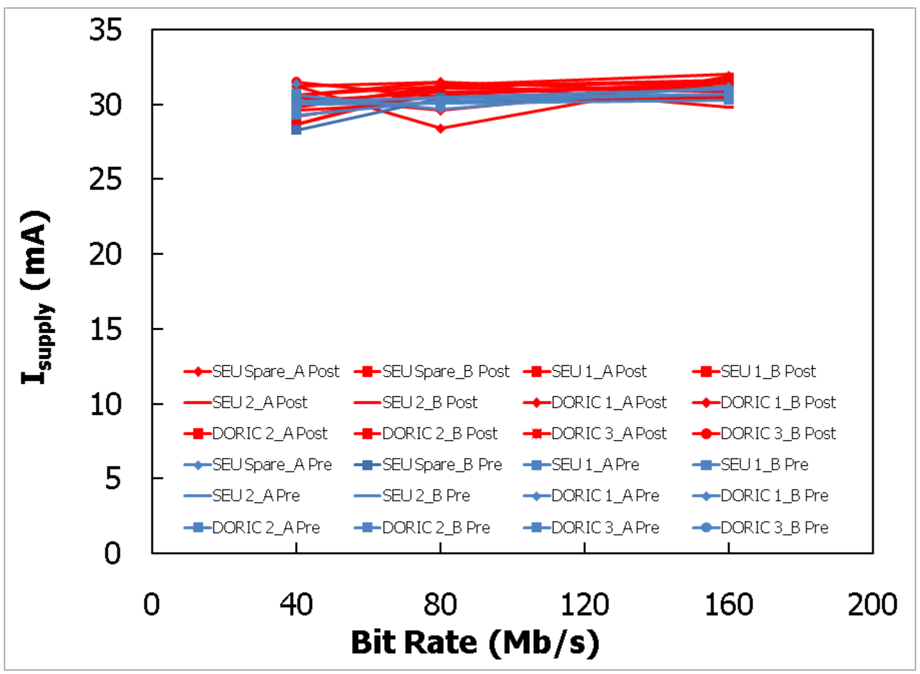
Threshold Shift in Irradiated PMOS

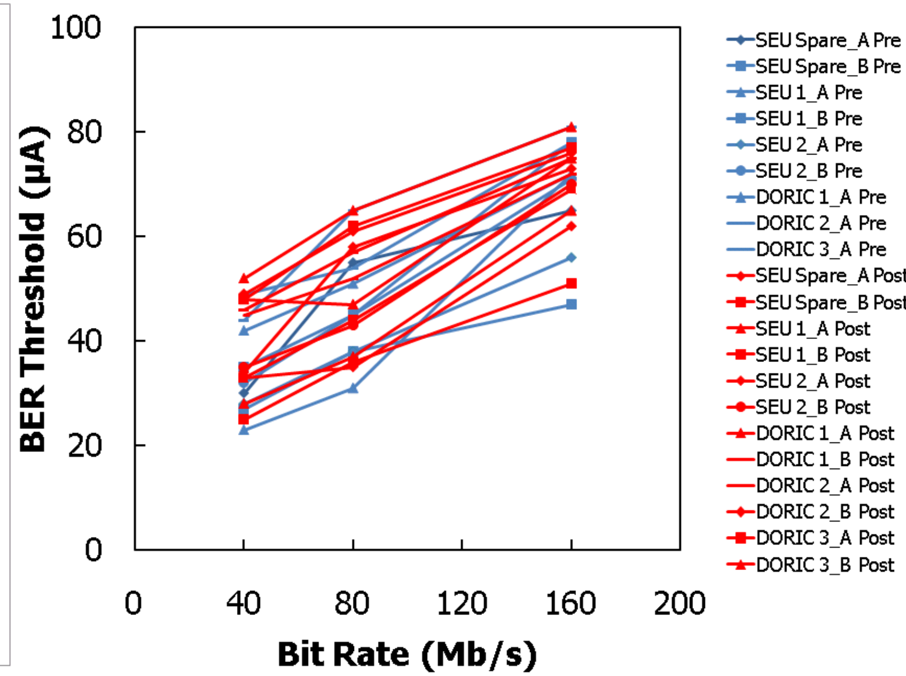


- Have access to two transistors for characterization
  - simulation with 300 mV threshold shift reproduces observed V vs. I
  - PMOS and NMOS have different threshold voltage shifts
  - ⇨ will use only PMOS in the current mirror

Receiver/Decoder Chip

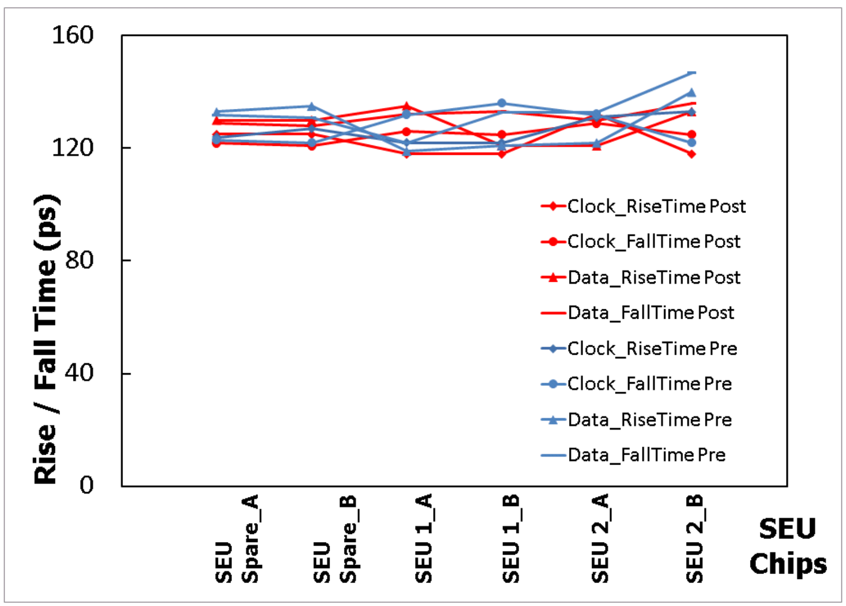
- Designed to operate at 40, 160, and 320 Mb/s
  - achieve only 250 Mb/s due to lack of time for design optimization before submission
  - no significant degradation up to SLHC dose

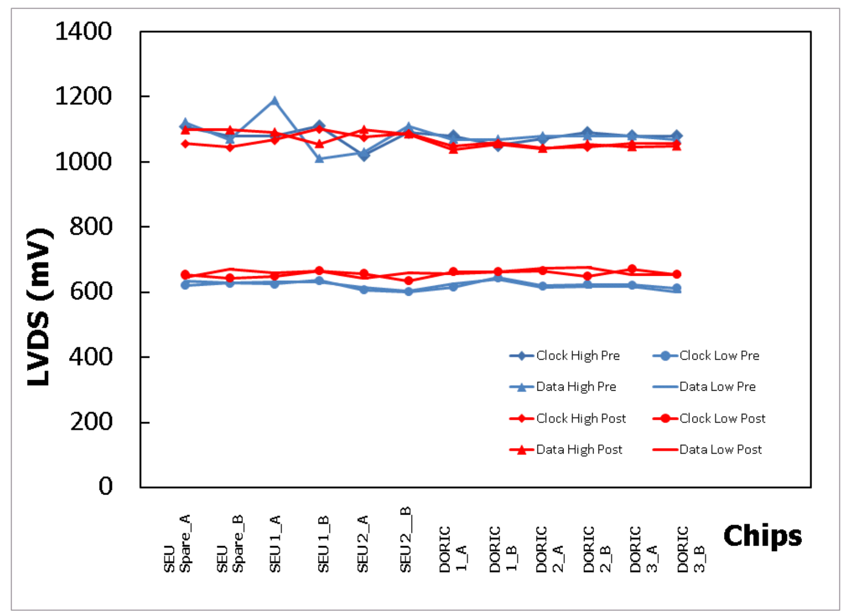




Low Voltage Differential Driver

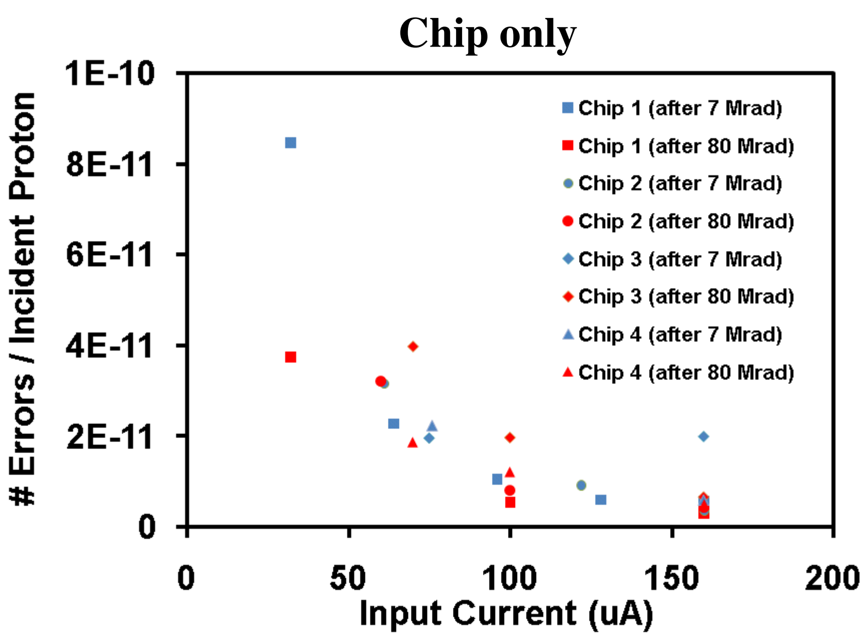
- output has fast rise and fall times
- output has proper amplitude and baseline
  - small clock jitter, e.g. < 50 ps (1%) @ 160 MHz
  - no significant degradation up to SLHC dose

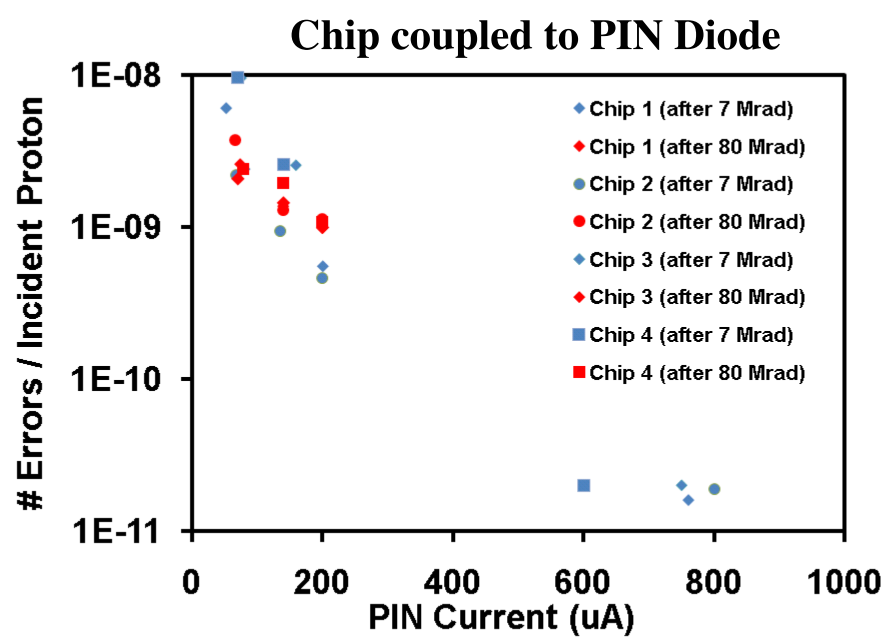




Single Event Upset

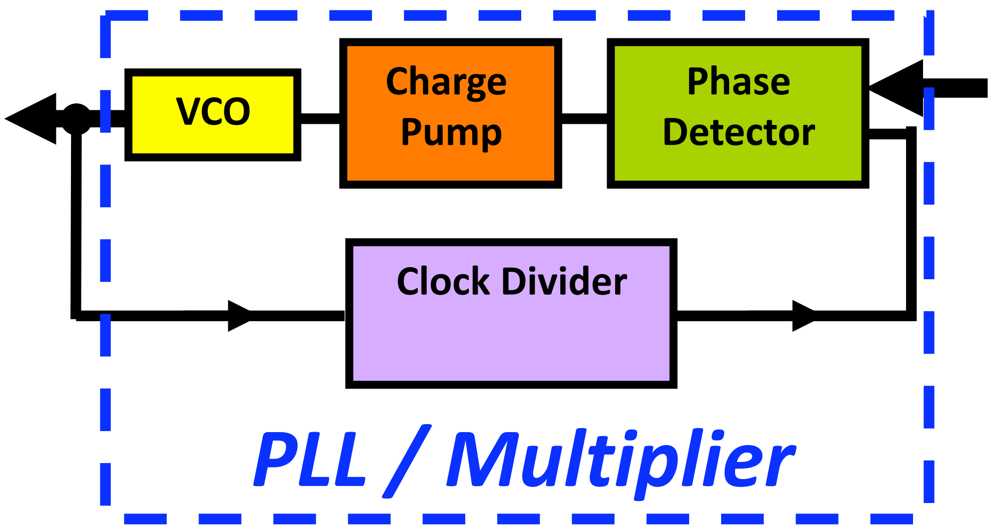
- Single event upset (SEU) measured with receiver/decoder coupled to a Taiwan PIN for 40 Mb/s operation
  - SEU rate much higher for chip coupled to PIN as expected
  - no significant degradation with radiation observed

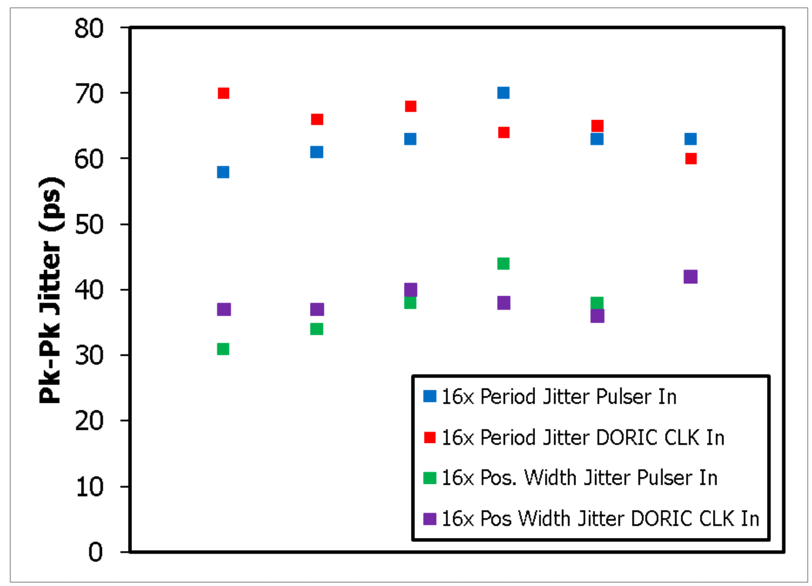




Clock Multiplier

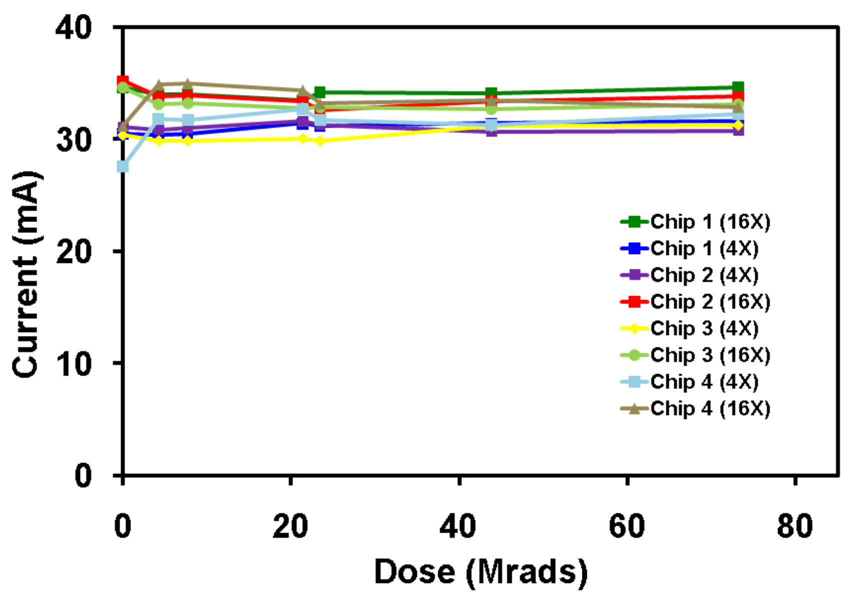
- clock multiplier needed to serialize high speed data
- both 4 x 160 MHz and 16 x 40 MHz clock multipliers work
  - use of recovered clock as input does not increase jitter

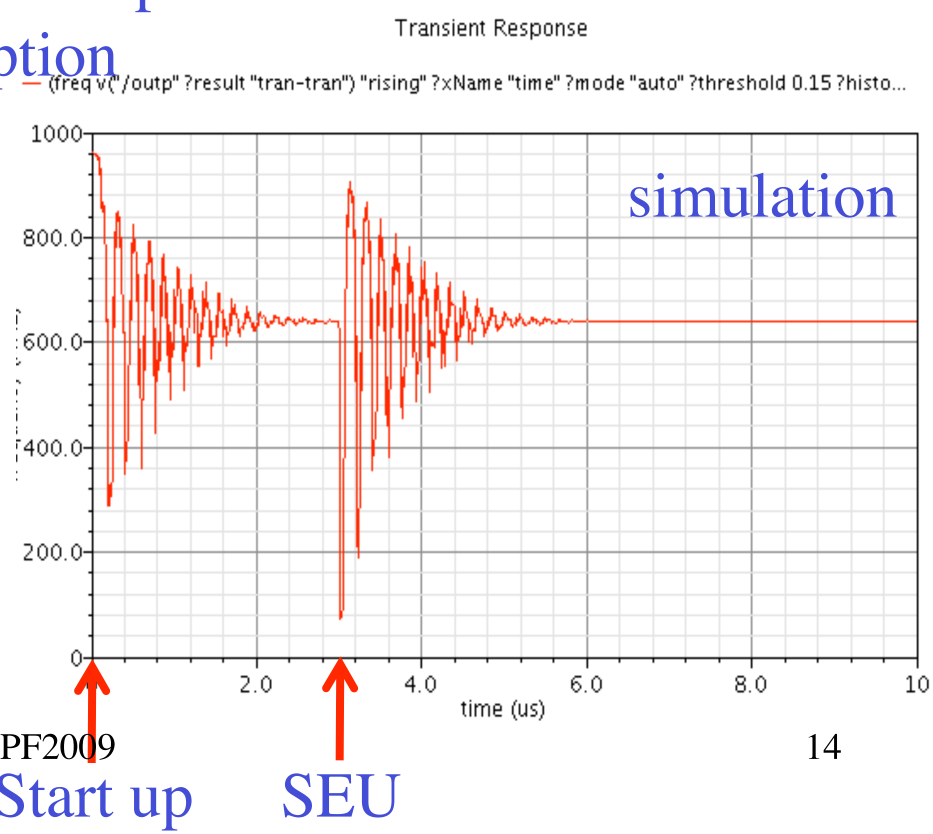




Clock Multiplier

- SEU in PIN coupled to data/clock decoder disturbed the input clock
  - ⇨ observation confirmed with simulation
  - ◆ output clock takes ~ 3 μs to recover
  - ◆ two of the four chips lost lock during irradiation
    - ❑ need power cycling to resume operation at 640 MHz
  - ◆ no change in current consumption





Summary

- first 130 nm submission mostly successful
- no significant degradation up to 73 Mrad
  - observe threshold shift in thick oxide transistors
- aim for next iteration in autumn 2009 with new functionalities
  - individual control of VCSEL currents
  - redundancy: ability to bypass a bad VCSEL/PIN channel

DPF 2009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